

**AMENDMENTS TO THE SPECIFICATION**

Please amend paragraphs [0020]-[0024] of the specification as follows:

[0020] Additional features and advantages of the invention will be set forth in the description which follows, and in part will be apparent from the description, or may be learned by practice of the invention. The objectives and other advantages of the invention will be realized and attained by the method particularly pointed out in the written description ~~and claims hereof~~ as well as the appended drawings.

[0021] To achieve these and other advantages and in accordance with the purpose of the present invention, as embodied and broadly described, a sequential lateral solidification (SLS) apparatus for crystallizing an amorphous silicon film includes a laser generator generating and emitting a laser beam; an X-Y stage corresponding to the laser generator and moving in two orthogonal axial directions; a mask arranged between the laser generator and the X-Y stage, the mask having a plurality of slits through which the laser beam passes; an objective lens arranged between the mask and the X-Y stage, the objective lens scaling down the laser beam; and a mask stage connected to the mask, the mask stage controlling a minute movement of the mask.

[0022] The above-mentioned apparatus further includes a condenser lens between the mask and the laser generator. Also, the condenser lens condenses the laser beam. In the above SLS apparatus, the X-Y stage is movable ~~rather long~~ longer way than the mask controlled by the mask stage.

[0023] In another aspect, a method of crystallizing an amorphous silicon film using the SLS apparatus includes the steps of setting a substrate having an amorphous silicon film thereon upon the X-Y stage; applying the laser beam to the amorphous silicon film after the laser beam passes through the plurality of slits of the mask; melting first portions of the amorphous silicon film, wherein each first portion of the amorphous silicon film corresponds to each slit of the mask; crystallizing the first portions of the amorphous silicon film by the sequential lateral solidification; moving the mask by several micrometers using the mask stage; repeatedly melting and crystallizing next portions of the amorphous silicon film adjacent to the first portions

whenever the mask [[moves]] is moved by the mask stage until a lateral grain growth stops by a collision of laterally grown grains, thereby defining a block in the amorphous silicon film; moving the X-Y stage having the substrate to crystallize another block of the amorphous silicon film; and repeatedly melting and crystallizing another blocks of the amorphous silicon film whenever the X-Y stage moves.

[0024] In the above method, the laser beam irradiates the amorphous silicon film whenever the mask [[moves]] is moved by the mask stage. Beneficially, the mask stage moves the mask in a direction of later grain growth by a distance of several micrometers which is equal to or less than the length of the lateral growth.